

## AMENDMENTS

Please amend the application as indicated hereafter.

### *In the Specification*

Please amend the specification as indicated below. The language being added is underlined (“    ”) and the language being deleted contains strikethrough (“~~—~~”):

For the paragraph 1, beginning on page 1:

This application is a division of ~~co-pending~~ U.S. Application Serial No. 09/855,972, filed May 15, 2001, now U.S. Patent No. 6,852,195, which is a division of U.S. Application Serial No. 08/932,025, entitled “Method And Apparatus For Low Energy Electron Enhanced Etching of Substrates in an AC or DC Plasma Environment”, filed September 17, 1997 now U.S. Pat. No. 6,258,287, which claims priority to and the benefit of the filing date of Provisional Patent Application Serial Nos. 60/026,985, filed September 20, 1996, entitled “APPARATUS AND PROCESS FOR LOW-DAMAGE DRY ETCHING OF INSULATORS BY LOW ENERGY ELECTRON ENHANCED ETCHING IN A DC PLASMA”; 60/026,587, filed September 20, 1996, entitled “APPARATUS AND PROCESS FOR LOW-DAMAGE DRY ETCHING OF INSULATORS BY LOW ENERGY ELECTRON ENHANCED ETCHING IN AN AC PLASMA”; and is a Continuation-In-Part of U.S. Patent Application Serial No. 08/705,902, filed on August 28, 1996 now U.S. Pat. No. 5,882,538 entitled “METHOD AND APPARATUS FOR LOW ENERGY ELECTRON ENHANCED ETCHING OF SUBSTRATES”.